



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#4/Amend A
4/12/02
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TECHNOLOGY CENTER 2800

Applicant(s): Han, K. Michael
Assignee: Advanced Micro Devices, Inc.
Title: Recessed Tunnel Oxide Profile For Improved Reliability In NAND Devices
Serial No.: 09/904,042 Filing Date: July 11, 2001
Examiner: Edward Wojciechowicz Group Art Unit: 2815
Docket No.: M-7468 US

Newport Beach, California
April 3, 2002

BOX AMENDMENT
COMMISSIONER FOR PATENTS
Washington, D. C. 20231

RESPONSE TO OFFICE ACTION

Dear Sir:

This responds to the Office Action mailed on January 3, 2002. Please amend the above-identified application as follows.

IN THE CLAIMS:

The following is a clean version of the entire set of pending claims. In accordance with 37 C.F.R. § 1.121(c)(1)(ii), Attachment A provides marked up versions of the claims containing the newly introduced changes. Please amend Claims 8, 9 and 10 as follows.

✓
Please cancel Claim 1-7.

SUB
B1

8. (Amended) A memory cell comprising:
a semiconductor substrate having a first region and a second region of one conduction type and a third region therebetween of an opposite conduction type;
a gate insulating layer formed over said substrate, the gate insulating layer having a first thickness formed over said first region and said second region, and a second thickness formed over said third region, said first thickness being greater than said second thickness;
and
a control gate formed on said gate insulating layer.

LAW OFFICES OF
SKJERVEN MORRILL
MACPHERSON LLP
25 METRO DRIVE
SUITE 700
SAN JOSE, CA 95110
(408) 453-9200
FAX (408) 453-7979